

Schottky barrier diode

RB081L-20

●Applications

High frequency rectification
For switching power supply

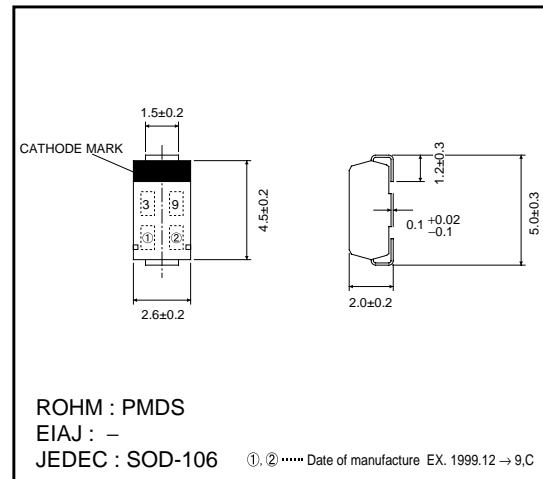
●Features

- 1) Compact power mold type. (PMDS)
- 2) Ultra low V_F . ($V_F=0.27V$ Typ. at 1A)
- 3) $I_o=5A$ guaranteed despite the size.

●Construction

Silicon epitaxial planar

●External dimensions (Units : mm)



●Absolute maximum ratings ($T_a=25^\circ C$)

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V_{RM}	25	V
DC reverse voltage	V_R	20	V
Mean rectifying current	I_{o1} *1	5	A
	I_{o2} *2	4	A
Peak forward surge current (60Hz 1 μ s)	I_{FSM}	70	A
Junction temperature	T_J	125	$^\circ C$
Storage temperature	T_{stg}	-40~+125	$^\circ C$

*1 When mounted on an alumina substrates (82×30×1.0mm), T_c Max.=90 $^\circ C$

*2 When mounted on an alumina substrates (82×30×1.0mm), $T_a=25^\circ C$

●Electrical characteristics ($T_a=25^\circ C$)

Parameter	Symbol	Typ.	Max.	Unit	Conditions
Forward voltage	V_F	-	0.45	V	$I_F=5.0A$
Reverse current	I_R	-	0.7	mA	$V_R=20V$

Diodes

● Electrical characteristics curves (Ta=25°C)

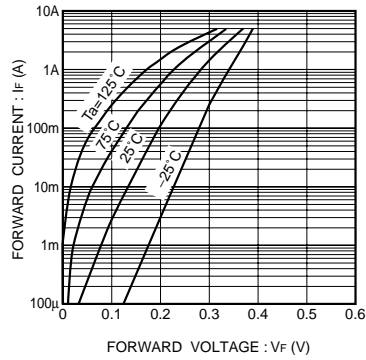


Fig.1 Forward characteristics

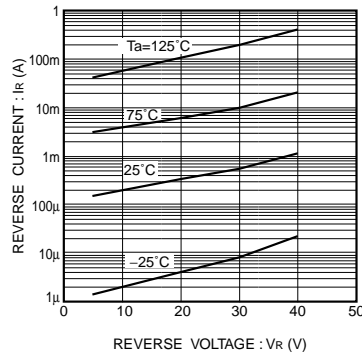


Fig.2 Reverse characteristics

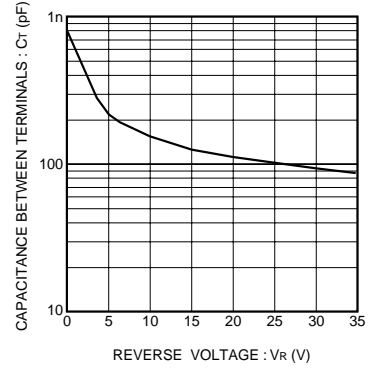


Fig.3 Capacitance between terminals characteristics

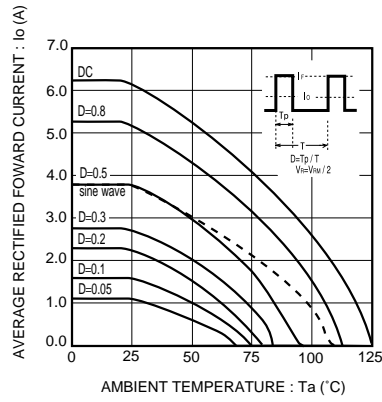


Fig.4 Derating curve (Io-Ta)

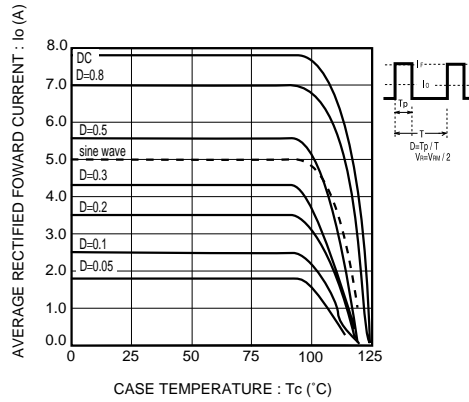


Fig.5 Derating curve (Io-Tc)